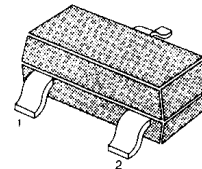


KST3906**PNP EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-200	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{STG}	150	°C

SOT-23



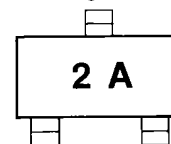
1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_A=25 °C)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -10 μ A, I _E =0	-40		V
*Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -1.0mA, I _B =0	-40		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =10 μ A, I _C =0	-5		V
Collector Cut-off Current	I _{CEX}	V _{CE} = -30V, V _{EB} = -3V		-50	nA
*DC Current Gain	h _{FE}	V _{CE} = -1V, I _C = -0.1mA	60		
		V _{CE} = -1V, I _C = -1mA	80		
		V _{CE} = -1V, I _C = -10mA	100	300	
		V _{CE} = -1V, I _C = -50mA	60		
		V _{CE} = -1V, I _C = -100mA	30		
*Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -10mA, I _B = -1mA		-0.25	V
		I _C = -50mA, I _B = -5.0mA		-0.4	V
*Base-Emitter Saturation Voltage	V _{BE} (sat)	I _C = -10mA, I _B = -1.0mA	-0.65	-0.85	V
		I _C = -50mA, I _B = -5.0mA		-0.95	V
Current Gain Bandwidth Product	f _T	I _C = -10mA, V _{CE} = -20V f=100MHz	250		MHz
Output Capacitance	C _{OB}	V _{CB} = -5V, I _E =0 f=1.0MHz		4.5	pF
Noise Figure	NF	I _C = -10 μ A, V _{CE} = -5V R _S =1k Ω f=10Hz to 15.7KHz		4	dB
Turn On Time	T _{ON}	V _{CC} = -3V, V _{BE} = -0.5V I _C = -10mA, I _{B1} = -1mA		70	ns
Turn Off Time	T _{OFF}	V _{CC} = -3V, I _C = -10mA I _{B1} =I _{B2} =1mA		300	ns

* Pulse Test: Pulse Width $\leq$ 300 μ s, Duty Cycle $\leq$ 2%

Marking



KST3906

PNP EPITAXIAL SILICON TRANSISTOR

